



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

2N5401

TO-92 Bipolar Transistor 双极型三极管

■ Features 特点

PNP High Voltage 高压

■ Absolute Maximum Ratings 最大额定值

TO-92

1. EMITTER

2. BASE

3. COLLECTOR



Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	-160	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	-150	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	-5	V
Collector Current 集电极电流	I_C	-600	mA
Power dissipation 耗散功率	$P_C(T_a=25^{\circ}C)$	625	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	200	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^{\circ}C$	

■ Device Rank 产品分档

Rank 档位	A	B
H_{FE} (2)Range	100-200	200-300

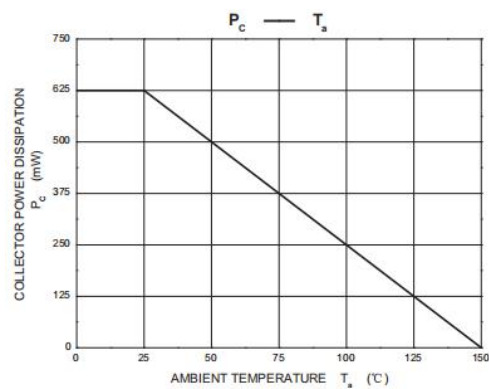
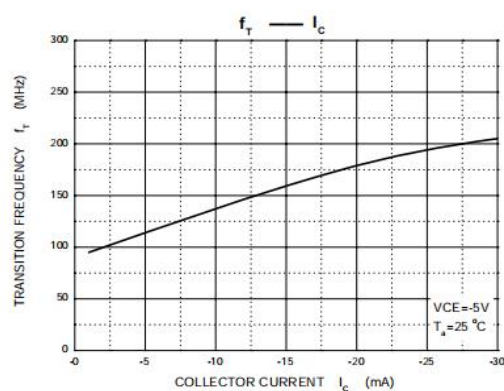
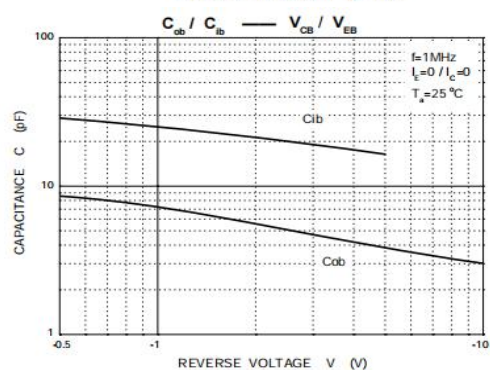
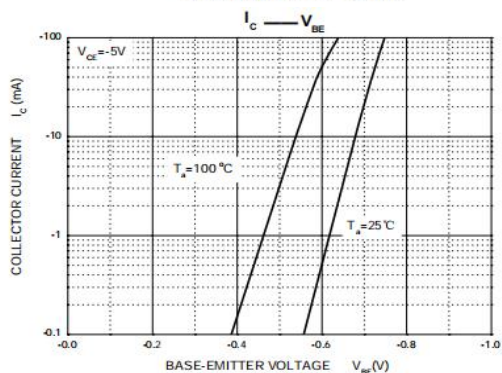
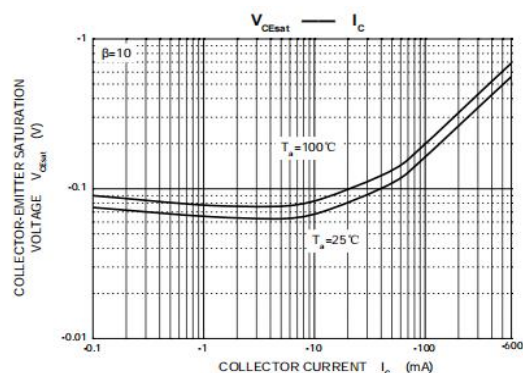
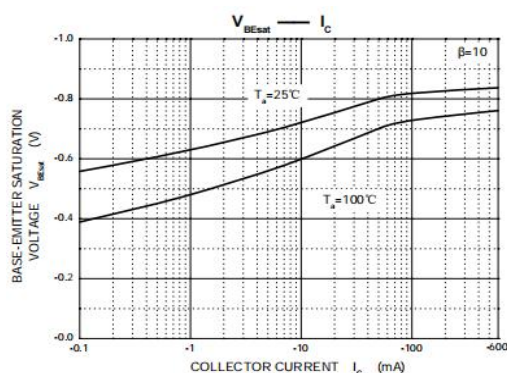
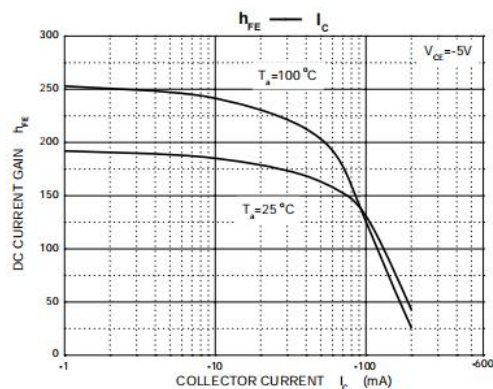
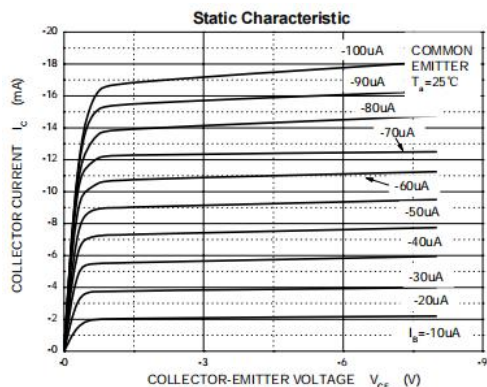


■Electrical Characteristics 电特性

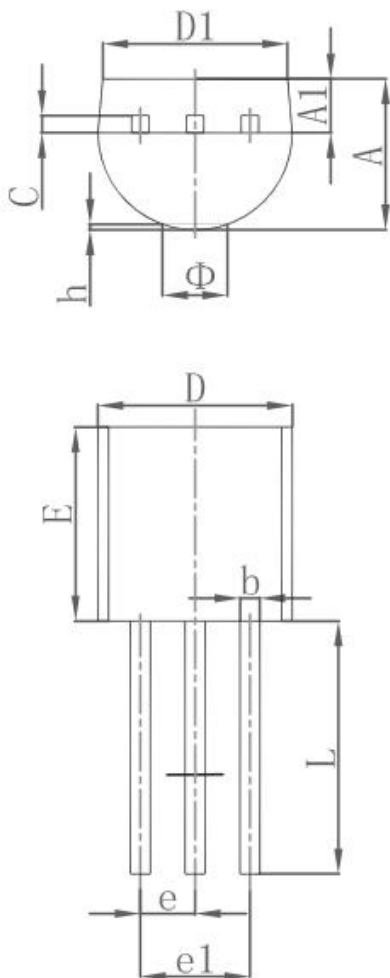
(TA=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压(I _C = -100μA, I _E =0)	BV _{CBO}	-160	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压(I _C = -1mA, I _B =0)	BV _{CEO}	-150	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压(I _E = -10μA, I _C =0)	BV _{EBO}	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流(V _{CB} = -160V, I _E =0)	I _{CBO}	—	—	-100	nA
Collector-Emitter Leakage Current 集电极发射极漏电流(V _{CE} = -120V, I _B =0)	I _{CEO}	—	—	-100	nA
Emitter-Base Leakage Current 发射极基极漏电流(V _{EB} = -5V, I _C =0)	I _{EBO}	—	—	-100	nA
DC Current Gain 直流电流增益(V _{CE} = -5V, I _C = -1mA)	H _{FE} (1)	80	—	—	
DC Current Gain 直流电流增益(V _{CE} = -5V, I _C = -10mA)	H _{FE} (2)	100	—	300	
DC Current Gain 直流电流增益(V _{CE} = -5V, I _C = -100mA)	H _{FE} (3)	50	—	—	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降(I _C = -10mA, I _B = -1mA) (I _C = -50mA, I _B = -5mA)	V _{CE(sat)}	—	—	-0.2 -0.5	V
Base-Emitter Saturation Voltage 基极发射极饱和压降(I _C = -10mA, I _B = -1mA) (I _C = -50mA, I _B = -5mA)	V _{BE(sat)}	—	—	-1 -1	V
Transition Frequency 特征频率(V _{CE} = -5V, I _C = -10mA)	f _T	100	—	—	MHz
Output Capacitance 输出电容(V _{CB} = -5V, I _E =0, f=1MHz)	C _{ob}	—	6	—	pF

Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015